

IN THE UNITED STATES PATENT AND TRA

Applicant(s): Beil et al.

Examiner:

Serial No.:

Not yet assigned

Group Art Unit:

Filed:

Herewith

Docket: 298-157

For:

DEVICE AND METHOD FOR

Dated: March 18, 2002

HIGH-SENSITIVITY RESOLUTION DETECTION

Assistant Commissioner for Patents Washington, D.C. 20231

LETTER

Sir:

Please make of record the art (copies enclosed) listed upon accompanying Form PTO-1449 and which was cited in the Search Report (copy enclosed)of the priority PCT application.

Streibl et al. were published after the priority date of the above-identified application.

Respectfully submitted,

Régistration No.: 28,375 Attorney for Applicant(s)

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CERTIFICATION UNDER 37 C.F.R. § 1.10

I hereby certify that this correspondence and the documents referred to as enclosed are being deposited with the United States Postal Service on date below in an envelope as "Express Mail Post Office to Addressee" Mail Label Number <u>EL918809416US</u> addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.

Dated: March 18, 2002

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